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PHOTOMULTIPLIER TUBE
R7154

High Sensitivity Solar Blind Photocathode (160 nm to 320 nm)
28 mm (1-1/8 Inch) Diameter, 9-stage, Side-on Type

FEATURES

- **Spectral Response ..... 160 nm to 320 nm**
- **Cathode Sensitivity**
  - **Radiant at 254 nm ..... 62 mA/W Typ.**
  - **Quantum Efficiency at 254 nm ..... 30 % Typ.**
- **Anode Sensitivity (at 1000 V)**
  - **Radiant at 254 nm ..... 6.2×10^5 A/W Typ.**

APPLICATIONS

- **Emission Spectroscopy**
- **UV Spectrophotometers**

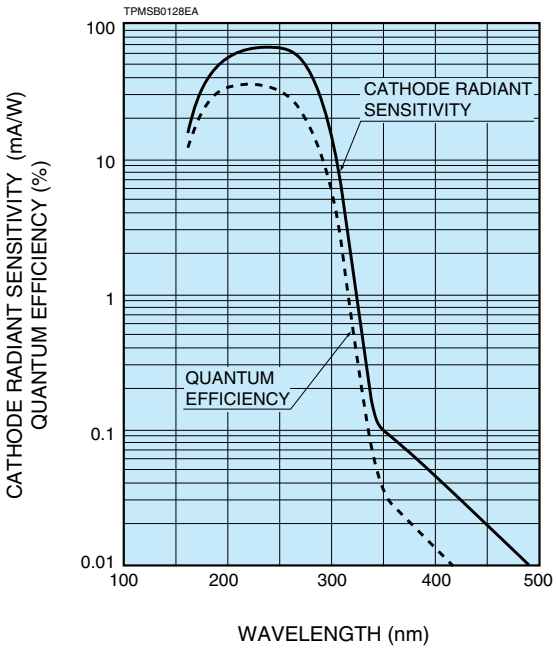
SPECIFICATIONS

GENERAL

Parameter		Description/Value	Unit
Spectral Response*		160 to 320	nm
Wavelength of Maximum Response		230	nm
Photocathode	Material	Cs-Te	—
	Minimum Effective Area	8 × 24	mm
Window Material		Quartz	—
Dynode	Secondary Emitting Surface	Sb-Cs	—
	Structure	Circular-cage	—
	Number of Stages	9	—
Direct Interelectrode Capacitances	Anode to Last Dynode	4	pF
	Anode to All Other Electrodes	6	pF
Base		11-pin base JEDEC No. B11-88	—
Weight		Approx. 45	g
Operating Ambient Temperature		-30 to +50	°C
Storage Temperature		-30 to +50	°C
Suitable Socket		E678–11A (Sold Separately)	—
Suitable Socket Assembly		E717–63 (Sold Separately)	—
		E717–74 (Sold Separately)	

* Operate in a nitrogen-purged environment for VUV detection.

Figure 1: Typical Spectral Response



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MAXIMUM RATINGS (Absolute Maximum Values)

Parameter		Value	Unit
Supply Voltage	Between Anode and Cathode	1250	V
	Between Anode and Last Dynode	250	V
Average Anode Current [A]		0.1	mA

CHARACTERISTICS (at 25 °C)

Parameter			Min.	Typ.	Max.	Unit
Cathode Sensitivity	Quantum Efficiency	at 254 nm	—	30	—	%
	Radiant	at 254 nm	—	62	—	mA/W
Anode Sensitivity	Radiant	at 254 nm	1.0×10^5	6.2×10^5	—	A/W
Gain			—	1.0×10^7	—	—
Anode Dark Current [F] (After 30 min Storage in Darkness)			—	1	10	nA
ENI (Equivalent Noise Input) [G]			—	9.1×10^{-17}	—	W
Time Response [E]	Anode Pulse Rise Time [H]		—	2.2	—	ns
	Electron Transit Time [I]		—	22	—	ns
	Transit Time Spread (TTS) [J]		—	1.2	—	ns
Anode Current Stability [K]	Light Hysteresis		—	0.1	—	%
	Voltage Hysteresis		—	1.0	—	%

NOTES

A: Averaged over any interval of 30 seconds maximum.

B: The light source is a tungsten filament lamp operated at a distribution temperature of 2856K. Supply voltage is 100 V between the cathode and all other electrodes connected together as anode.

C: Red/White ratio is the quotient of the cathode current measured using a red filter (Toshiba R-68) interposed between the light source and the tube by the cathode current measured with the filter removed under the same conditions as Note B.

D: The value is cathode output current when a blue filter (Corning CS 5-58 polished to 1/2 stock thickness) is interposed between the light source and the tube under the same condition as Note B.

E: Measured with the same light source as Note B and with the voltage distribution ratio shown in Table 1 below.

Table 1: Voltage Distribution Ratio

Electrode	K	Dy1	Dy2	Dy3	Dy4	Dy5	Dy6	Dy7	Dy8	Dy9	P
Distribution Ratio	1	1	1	1	1	1	1	1	1	1	

Supply Voltage: 1000 V, K: Cathode, Dy: Dynode, P: Anode

F: Measured with the same supply voltage and voltage distribution ratio as Note E after removal of light.

G: ENI is an indication of the photon-limited signal-to-noise ratio. It refers to the amount of light in watts to produce a signal-to-noise ratio of unity in the output of a photomultiplier tube.

$$ENI = \frac{\sqrt{2q \cdot Idb \cdot G \cdot \Delta f}}{S}$$

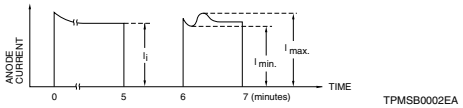
where q = Electronic charge (1.60×10^{-19} coulomb).
Idb = Anode dark current (after 30 minute storage) in amperes.
G = Gain.
Δf = Bandwidth of the system in hertz. 1 hertz is used.
S = Anode radiant sensitivity in amperes per watt at the wavelength of peak response.

H: The rise time is the time for the output pulse to rise from 10 % to 90 % of the peak amplitude when the entire photocathode is illuminated by a delta function light pulse.

I: The electron transit time is the interval between the arrival of delta function light pulse at the entrance window of the tube and the time when the anode output reaches the peak amplitude. In measurement, the whole photocathode is illuminated.

J: Also called transit time jitter. This is the fluctuation in electron transit time between individual pulses in the signal photoelectron mode, and may be defined as the FWHM of the frequency distribution of electron transit times.

K: Hysteresis is temporary instability in anode current after light and voltage are applied.



$$\text{Hysteresis} = \frac{I_{max.} - I_{min.}}{I_i} \times 100\ (\%)$$

(1) Light Hysteresis
The tube is operated at 750 V with an anode current of 1 μA for 5 minutes. The light is then removed from the tube for a minute. The tube is then re-illuminated by the previous light level for a minute to measure the variation.

(2) Voltage Hysteresis
The tube is operated at 300 V with an anode current of 0.1 μA for 5 minutes. The light is then removed from the tube and the supply voltage is quickly increased to 800 V. After a minute, the supply voltage is then reduced to the previous value and the tube is re-illuminated for a minute to measure the variation.

Figure 2: Anode Radiant Sensitivity and Gain Characteristcs

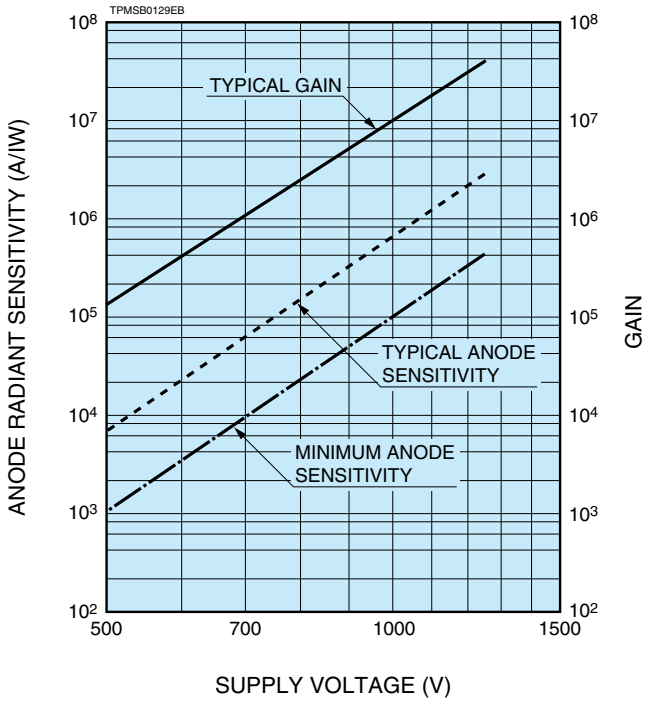


Figure 3: Typical Time Response

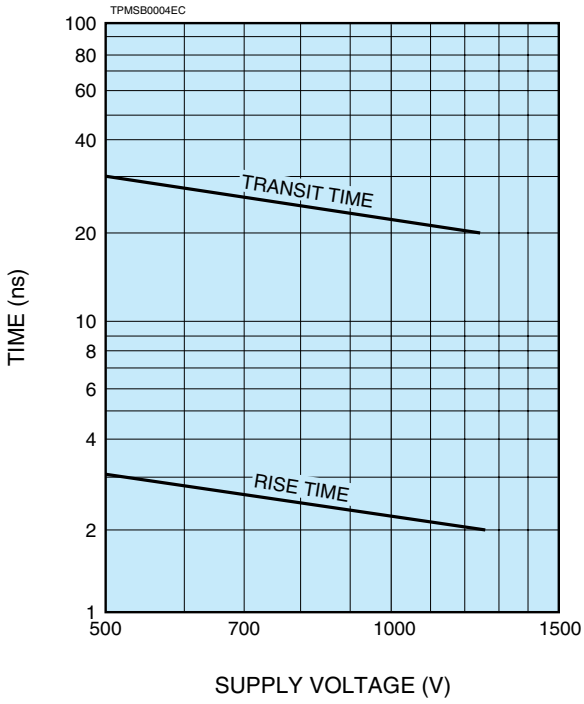


Figure 4: Dimensional Outline and Basing Diagram (Unit: mm)

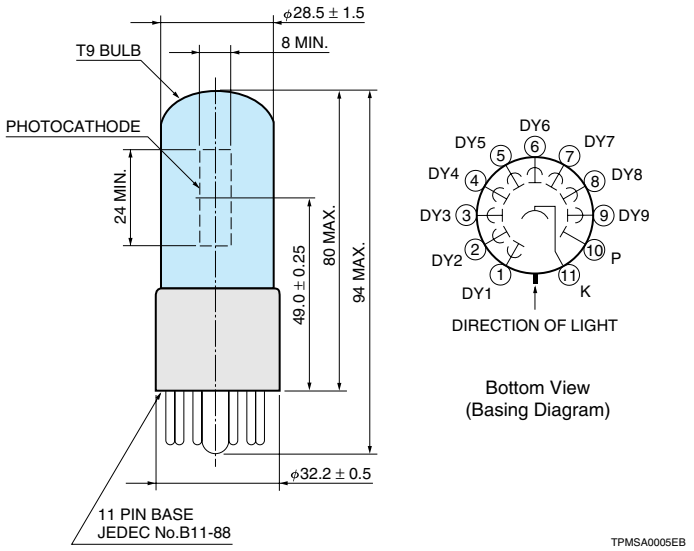


Figure 5: Socket (Unit: mm) Sold Separately

E678-11A

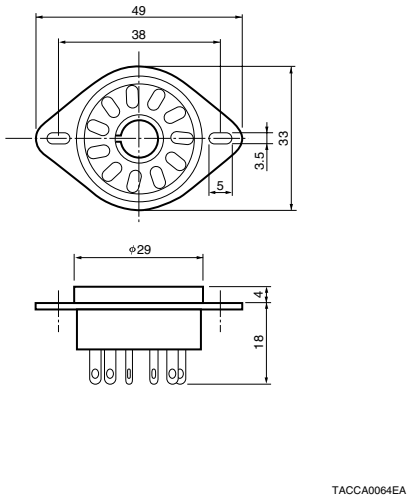
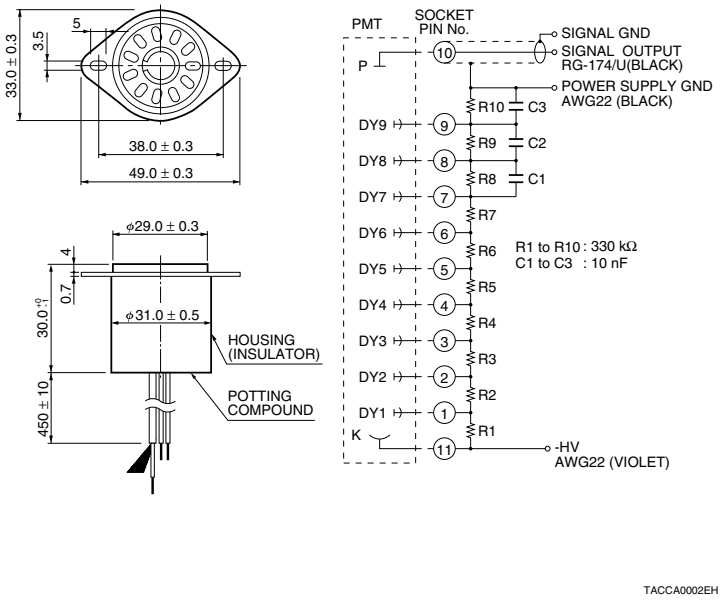
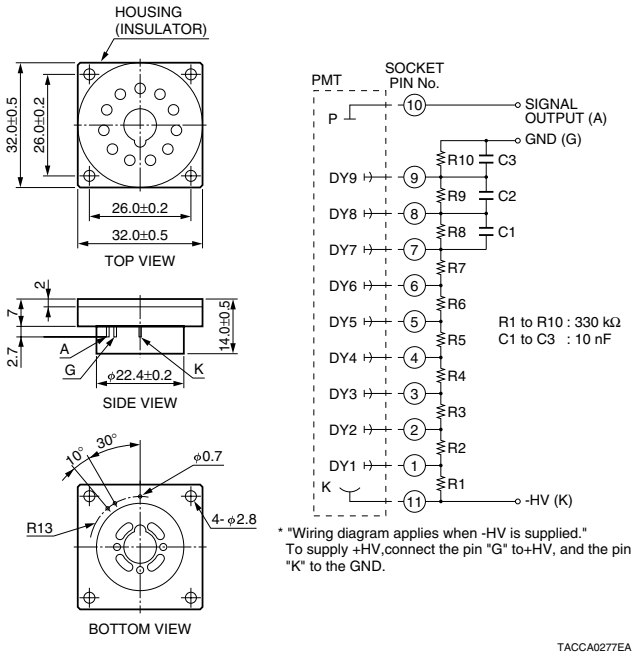


Figure 6: D Type Socket Assembly (Unit: mm) Sold Separately

E717-63



E717-74



* Hamamatsu also provides C4900 series compact high voltage power supplies and C6270 series DP type socket assemblies which incorporate a DC to DC converter type high voltage power supply.

Warning–Personal Safety Hazards

Electrical Shock–Operating voltages applied to this device present a shock hazard.

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